

In The Specification

The text inserted at p.1, prior to the Technical Field section, by the preliminary amendment dated January 18, 1999, has been amended to read as shown below:

D¹ This patent resulted from a divisional application of U.S. Patent Application Serial No. 08/748,997, filed November 14, 1996, entitled "Method Of Forming A Crystalline Phase Material", naming Gurtej S. Sandhu and Sujit Sharan as inventors, and which is now U.S. Patent No. 5,997,634, the disclosure of which is incorporated by reference.

The paragraph extending from p. 14, line 3, to p. 14, line 13, has been replaced with the paragraph shown below:

D² Another alternate embodiment is described with reference to Figs. 10-12 whereby the stress inducing layer is provided over or outwardly of, and thereby operatively adjacent, the titanium layer prior to its initial transformation to the first C49 crystalline phase. Fig. 10 illustrates a semiconductor wafer fragment 50 comprised of a bulk monocrystalline silicon substrate 52 and an overlying insulating layer 54, such as SiO₂. A polysilicon layer 56 is provided outwardly of layer 54, with a refractory metal layer 58, such as titanium, provided outwardly of polysilicon layer 56. A compressive stress inducing layer 60 is provided over and on titanium layer 58 and preferably has a thickness equal to or greater than the combined thickness of layers 56 and 58.